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10NT74

Seventh Semester B.E. Degree Examination, Dec.2016/Jan.2017
Thin Film Technology

Time: 3 hrs.

Max. Marks:100

Note: Answer any FIVE full questions, selecting atleast TWO questions from each part

PART – A

- 1 a. Write a brief note on inter – diffusion, grain boundary diffusions. (05 Marks)
b. Explain Lattice matching epitaxy and domain matching epitaxy. (07 Marks)
c. Explain Thin film nucleation and growth models. (08 Marks)
- 2 a. Explain the Spin coating process, with neat diagram. (08 Marks)
b. Explain the process of MOCVD giving an example. Mention its applications. (07 Marks)
c. Write a note on Electron plating, with an example. (05 Marks)
- 3 a. What is Epitaxy? Explain epitaxial thin films LPE and MBE, with neat diagram. (12 Marks)
b. Define Sputtering deposition. Discuss in detail Reactive sputtering. (08 Marks)
- 4 a. Write about the following electrical methods to measure the thickness of the thin films :
i) Film Resistance ii) Capacitance monitors. (12 Marks)
b. Brief the capillarity theory of thin film nucleation. (08 Marks)

PART – B

- 5 a. Write about Electron transport phenomenon in semiconductors. (12 Marks)
b. Explain Electron transportation in single electron transistors. (08 Marks)
- 6 a. Explain in detail screen printing. (10 Marks)
b. Write a note on Gravure printing. (10 Marks)
- 7 a. Explain about Molecular beam epitaxy technique, with neat sketch. (10 Marks)
b. Describe Atomic Layer deposition technique, with diagram. (10 Marks)
- 8 a. Explain the applications if thin films as a photo detector. (10 Marks)
b. Describe the use of thin films in solar cells. (10 Marks)

Important Note
1. On completing your answers compulsorily draw diagonal cross lines on the remaining blank pages.
2. Any revealing of identification, appeal to evaluator and /or equations written eg. 42+8=50, will be treated as malpractice.